

WHAT IS CLAIMED IS:

1. A group III nitride compound semiconductor light-emitting device comprising:  
a semiconductor laminate portion containing a  
5 light-emitting layer; and  
a groove formed in said semiconductor laminate portion so as to extend from a light emission observation surface of said semiconductor laminate portion to reach at least said light-emitting layer.

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2. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is distributed equally in said light emission observation surface.

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3. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said groove is formed by etching.

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4. A group III nitride compound semiconductor light-emitting device according to claim 3, wherein an n-type seat electrode-forming surface is provided at a level equal to a bottom of said groove.

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5. A group III nitride compound semiconductor

light-emitting device comprising:

a substrate;

a semiconductor laminate being laminated on said substrate  
and comprising a plurality of group III nitride compound  
5 semiconductor layers, said semiconductor laminate including at  
least a light-emitting region; and

a groove formed in said semiconductor laminate so as to  
extend within a plane of a light emission observation surface  
of said semiconductor laminate, said groove having a depth to  
10 reach said light-emitting region to thereby reveal said  
light-emitting region on a side surface of said groove.

6. A group III nitride compound semiconductor  
light-emitting device according to claim 5, wherein a width of  
15 said groove is in a range of from 0.5 to 30  $\mu\text{m}$ .

7. A group III nitride compound semiconductor  
light-emitting device according to claim 5, further comprising  
an n-type seat electrode-forming surface formed in said  
20 semiconductor laminate and adapted to mount an n-type seat  
electrode, wherein a bottom surface of said groove is located  
substantially at the same height level as said n-type seat  
electrode-forming surface.

25 8. A group III nitride compound semiconductor

light-emitting device according to claim 5, further comprising  
a p-type seat electrode and an n-type seat electrode, and said  
semiconductor laminate has a plurality of current diffusion paths  
formed between said p-type seat electrode and said n-type seat  
5 electrode and each being divided by said groove, all of said  
current diffusion paths having substantially same lengths and  
same widths.

9. A group III nitride compound semiconductor  
10 light-emitting device comprising:

a substrate; and  
a plurality of semiconductor layer blocks formed on said  
substrate, each of said semiconductor layer blocks having a  
light-emitting region revealed on a side surface thereof.

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10. A group III nitride compound semiconductor  
light-emitting device according to claim 9, further comprising  
a p-type seat electrode formed on one of said semiconductor layer  
blocks and an auxiliary electrode extending from said p-type  
20 seat electrode to another semiconductor layer block.

11. A group III nitride compound semiconductor  
light-emitting device according to claim 10, further comprising  
an insulating layer formed between said semiconductor layer block  
25 and said auxiliary electrode.